Abstracts

GaAs IC's Fabricated with the High-Performance, High-Yield Multifunction Self-Aligned Gate Process for Radar and EW Applications

I.J. Bahl, D.A. Willems, J.F. Naber, H.P. Singh, E.L. Griffin, M.D. Pollman, A.E. Geissberger and R.A. Sadler. "GaAs IC's Fabricated with the High-Performance, High-Yield Multifunction Self-Aligned Gate Process for Radar and EW Applications." 1990 Transactions on Microwave Theory and Techniques 38.9 (Sep. 1990 [T-MTT] (Special Issue on Multifunction MMIC's and their System Applications)): 1232-1241.

This paper presents design and test results for several multiuse GaAs IC's for radar and EW applications. The chips described are a redundant switch, a broad-band distributed amplifier, a broad-band variable-gain amplifier, a 2.5 GHz sample and hold, a 1 GHz analog-to-digital converter, and an L-band buffered prescaler. These IC's, fabricated with the ITT 0.4-µm-gate MESFET multifunction self-aligned gate (MSAG) process, demonstrated excellent performance.

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